



**THE DATASHEET OF
NVD6416ANT4G-VF01**



NTD6416AN, NVD6416AN

MOSFET – Power, N-Channel

100 V, 17 A, 81 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	100	V	
Gate-to-Source Voltage – Continuous		V_{GS}	± 20	V	
Continuous Drain Current	Steady State	I_D	$T_C = 25^\circ\text{C}$	17	A
			$T_C = 100^\circ\text{C}$	11	
Power Dissipation	Steady State	P_D	$T_C = 25^\circ\text{C}$	71	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	62	A	
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	17	A	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50 \text{ Vdc}$, $V_{GS} = 10 \text{ Vdc}$, $I_{L(pk)} = 17 \text{ A}$, $L = 0.3 \text{ mH}$, $R_G = 25 \Omega$)		E_{AS}	43	mJ	
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	2.1	$^\circ\text{C/W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	

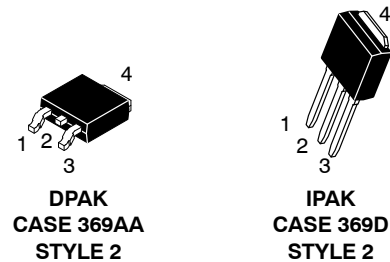
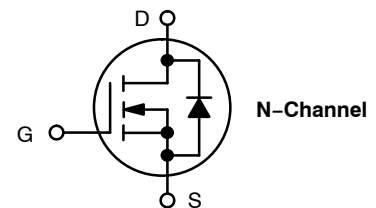
1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).



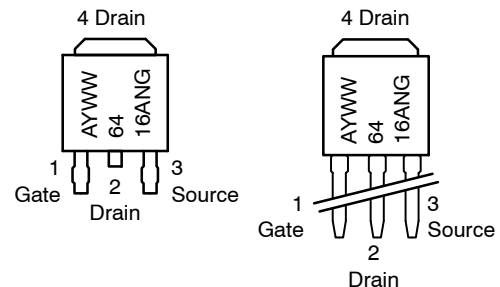
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
100 V	81 mΩ @ 10 V	17 A



MARKING DIAGRAM & PIN ASSIGNMENTS



A = Assembly Location*
 Y = Year
 WW = Work Week
 6416AN = Device Code
 G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100			V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			112		mV/°C	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$	$T_J = 25^\circ\text{C}$			1.0	μA
			$T_J = 125^\circ\text{C}$			10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$				± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	2.0		4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			7.7		mV/°C
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 17\text{ A}$		73	81	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 10\text{ A}$		12		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		620		pF	
Output Capacitance	C_{OSS}			110			
Reverse Transfer Capacitance	C_{RSS}			50			
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 80\text{ V}, I_D = 17\text{ A}$		20		nC	
Threshold Gate Charge	$Q_{G(TH)}$			1.0			
Gate-to-Source Charge	Q_{GS}			3.6			
Gate-to-Drain Charge	Q_{GD}			10			
Plateau Voltage	V_{GP}			5.8			V
Gate Resistance	R_G			2.4			Ω

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DD} = 80\text{ V}, I_D = 17\text{ A}, R_G = 6.1\ \Omega$		9.2		ns
Rise Time	t_r			22		
Turn-Off Delay Time	$t_{d(off)}$			24		
Fall Time	t_f			20		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 17\text{ A}$	$T_J = 25^\circ\text{C}$		0.85	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{rr}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 17\text{ A}$		56		ns	
Charge Time	t_a			41			
Discharge Time	t_b			15			
Reverse Recovery Charge	Q_{RR}			135			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

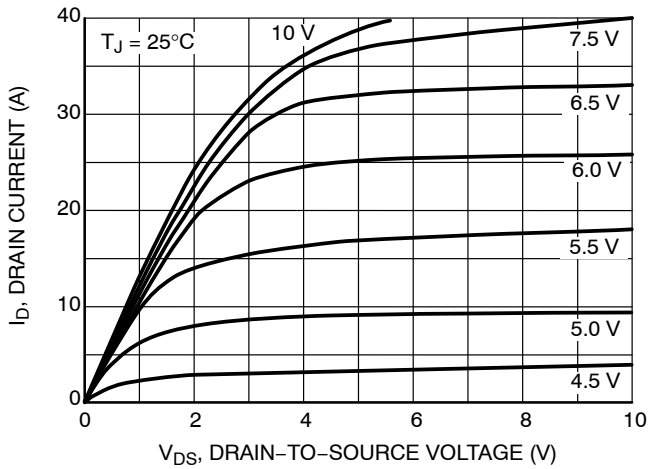


Figure 1. On-Region Characteristics

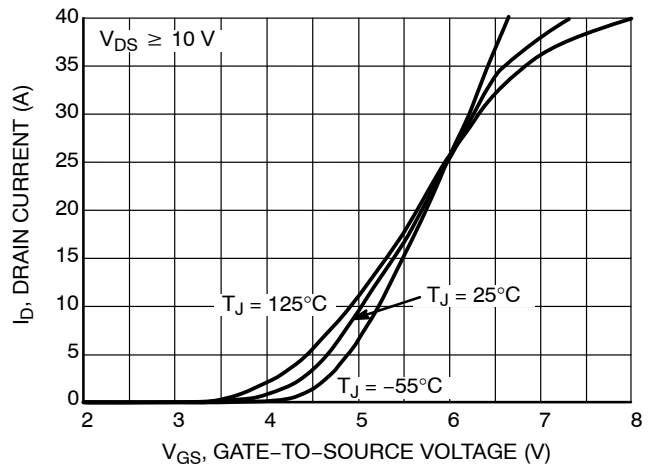


Figure 2. Transfer Characteristics

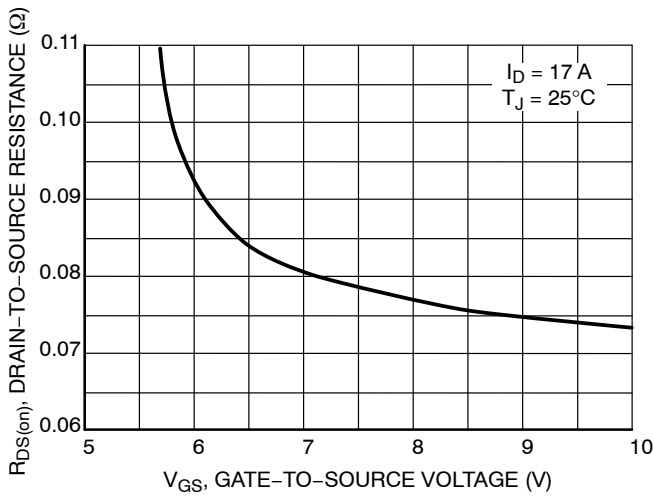


Figure 3. On-Region versus Gate Voltage

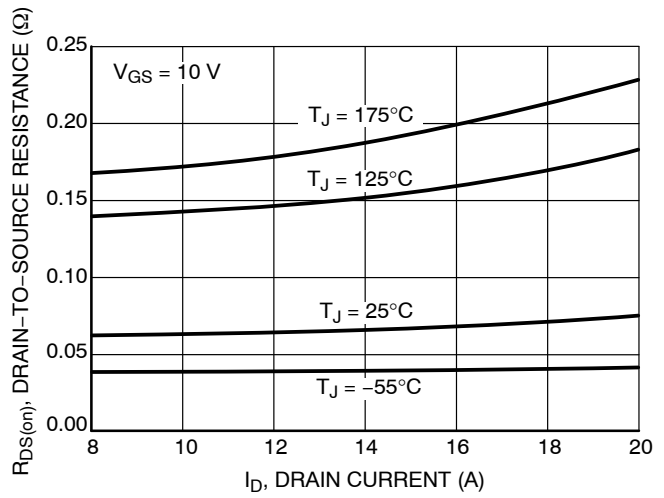


Figure 4. On-Resistance versus Drain Current and Gate Voltage

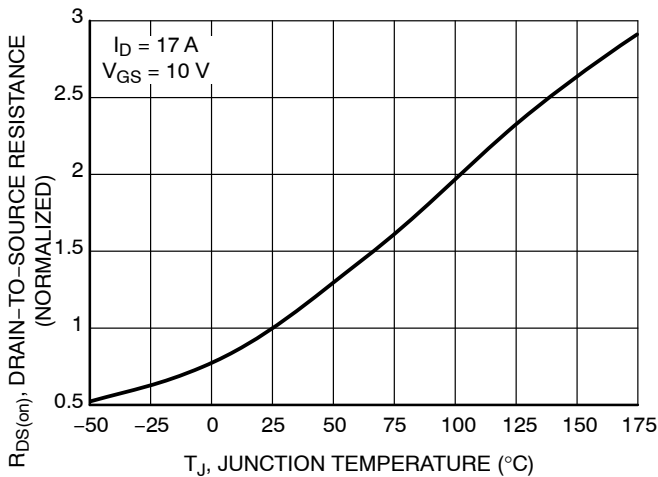


Figure 5. On-Resistance Variation with Temperature

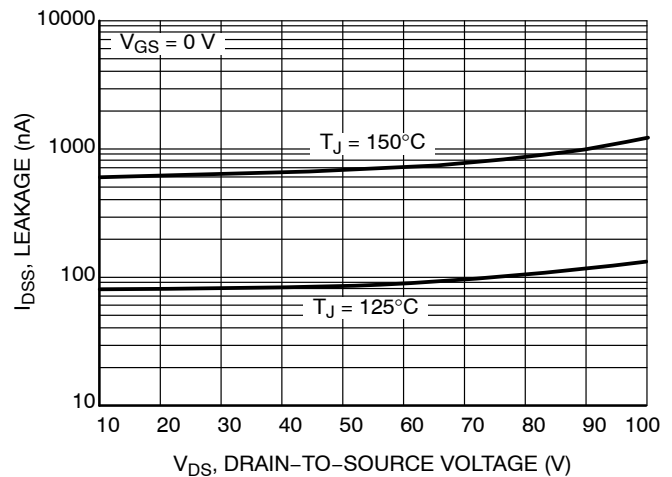


Figure 6. Drain-to-Source Leakage Current versus Voltage

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TYPICAL CHARACTERISTICS

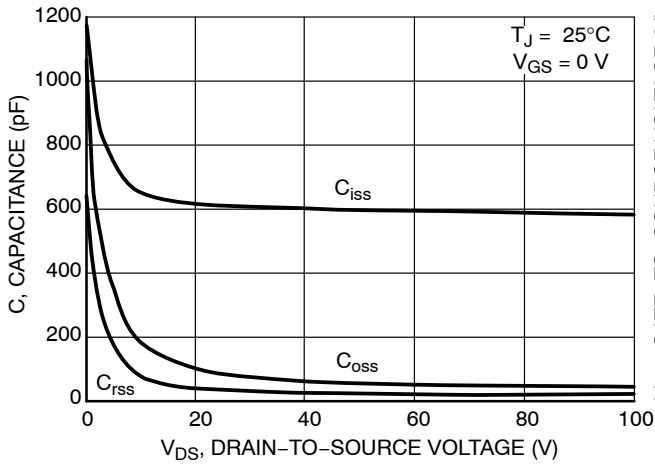


Figure 7. Capacitance Variation

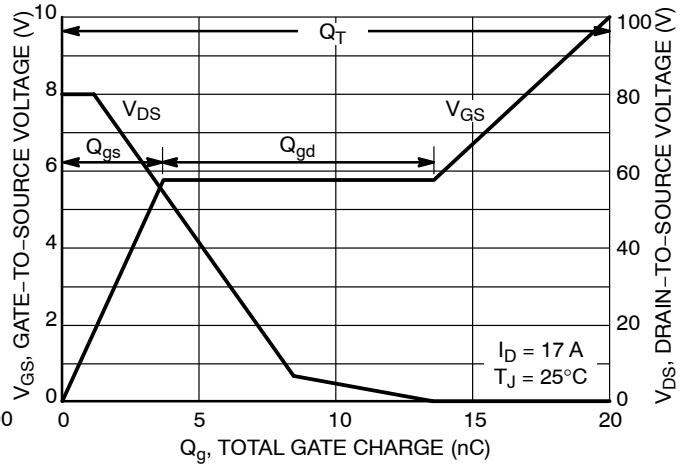


Figure 8. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

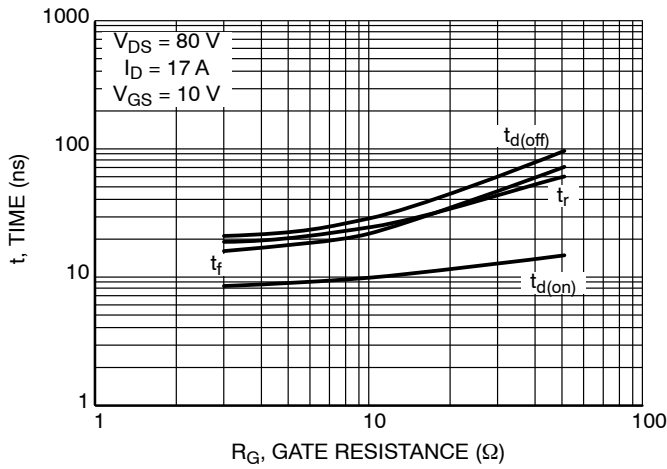


Figure 9. Resistive Switching Time Variation versus Gate Resistance

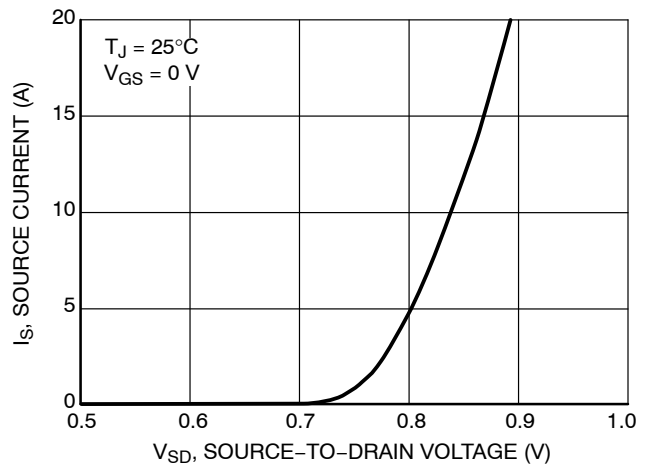


Figure 10. Diode Forward Voltage versus Current

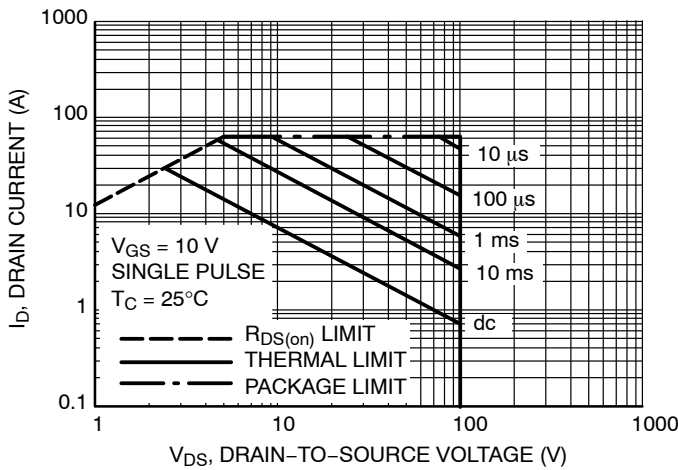


Figure 11. Maximum Rated Forward Biased Safe Operating Area

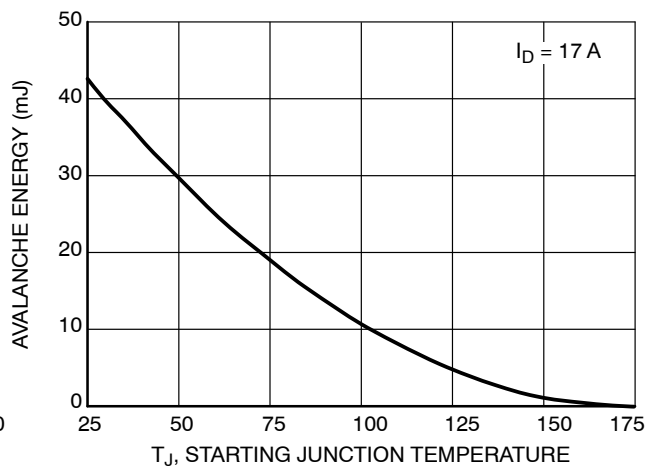


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

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TYPICAL CHARACTERISTICS

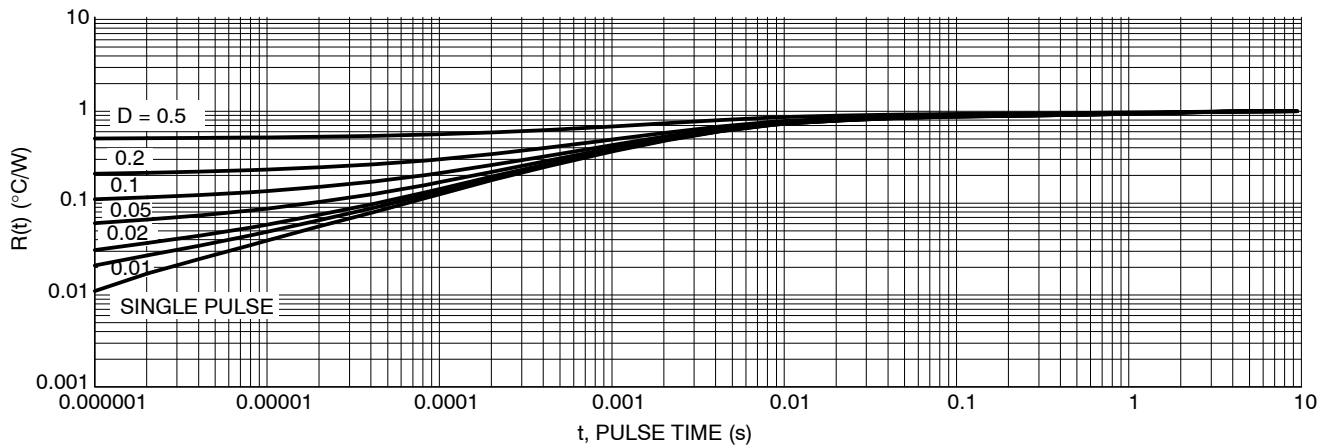


Figure 13. Thermal Response

ORDERING INFORMATION

Device	Package	Shipping†
NTD6416ANT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD6416AN-1G	IPAK (Pb-Free)	75 Units / Rail
NVD6416ANT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

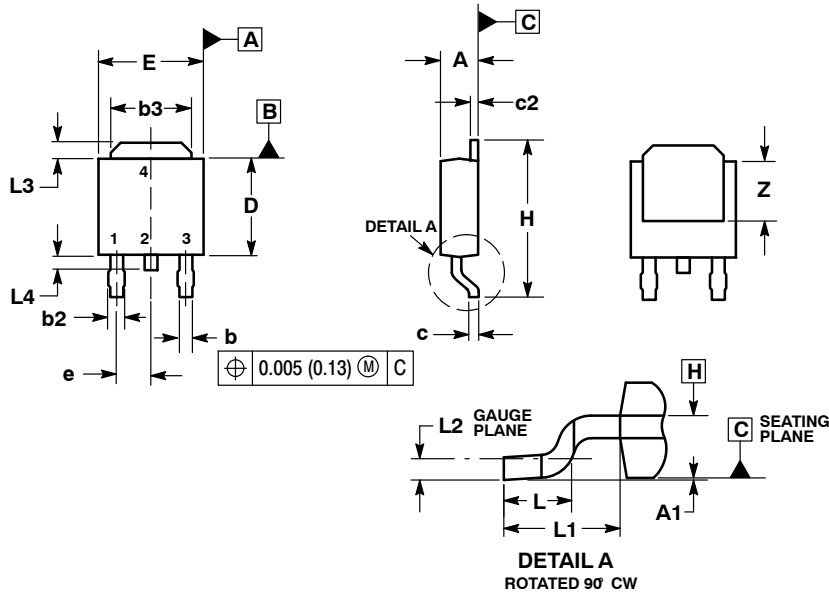
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

NTD6416AN, NVD6416AN

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE) CASE 369AA ISSUE B



NOTES:

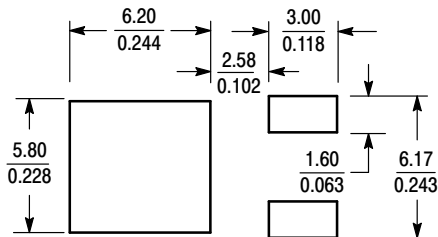
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

SOLDERING FOOTPRINT*



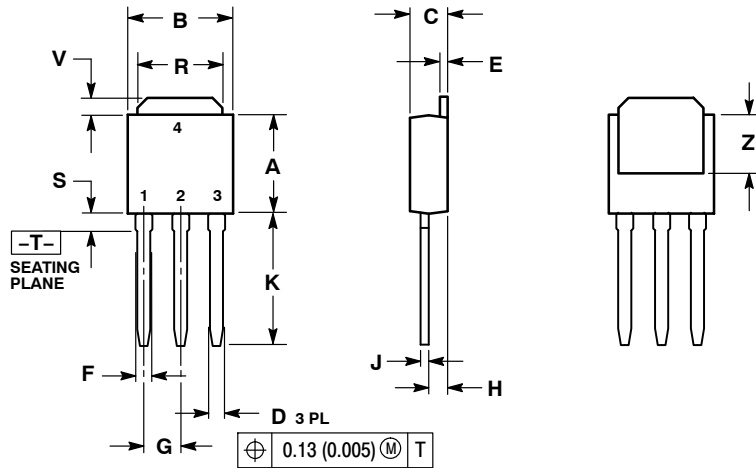
SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1: GATE
 PIN 2: DRAIN
 PIN 3: SOURCE
 PIN 4: DRAIN

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